

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)					Attorney Docket Number 5308-156	Serial No. 09/911,995	
					Applicants: Ryu et al.		
					Filing Date: July 24, 2001	Group: 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>JKTH</i>	1	5,972,801	10/26/99	Lipkin et al.	438	770	—
<i>JKTH</i>	2	6,165,822	12/26/00	Okuno et al.	438	142	—
<i>JKTH</i>	3	2002/0072247A1	6/13/02	Lipkin et al.	438	767	✓
FOREIGN PATENT DOCUMENTS							
	4	Document No.	Date	Country	Class	Subclass	Translation
<i>JKTH</i>	5	JP02000252461A	9/14/00	Japan	—	—	Abstract
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>JKTH</i>	6	Copy of International Search Report for PCT/US02/11691 dated 12/4/02.					
<i>JKTH</i>	7	G.Y. Chung, C.C. Tin, J.R. Williams, K. McDonald, R.A. Weller, S.T. Pantelides, L.C. Feldman, M.K. Das, and J.W. Palmour, "Improved Inversion Channel Mobility for 4H-SiC MOSETs Following High-Temperature Anneals in Nitric Oxide," IEEE Electron Device Letters accepted for publication, 2000.					
<i>X</i>	8	Das, Mrinal K. Graduate thesis entitled, Fundamental Studies of the Silicon Carbide MOS Structure. Purdue University, 1999.					
	9	Xu et al. "Improved Performance and Reliability of N₂O Grown Oxynitride on 6H-SiH," IEEE Electron Device Letters. Vol. 21, No. 6, June 2000, p. 298-300.					
<i>JKTH</i>	10	Wang et al. "High Temperature Characteristics of High Quality SiC MIS Capacitors with O/N/O Gate Dielectric," IEEE Transactions on Electron Devices. Vol. 47, No. 2, February 2000, pp. 458-462.					
	11	Lai et al. "Interface Properties of N₂O Annealed NH₃ Treated 6H-SiC MOS Capacitor," Electron Devices Meeting, June 26, 1999, pp. 469.					
	12	Lipkin et al. "Challenges and State of the Art of Oxides on SiC," Mat. Res. Symp. Proc. Vol. 640, 2001.					
<i>JKTH</i>	13	Cho et al. "Improvement of charge trapping by hydrogen post-oxidation annealing in gate oxide of 4H-SiC methel-oxide-semiconductor capacitors," Applied Physics Letters. Vol. 77, No. 8, pp. 1215-7.					
	14	Fukuda et al. "Improvement of SiO ₂ /4H-SiC Interface Using High-Temperature Hydrogen Annealing at Low Pressure and Vacuum Annealing," Jpn J. Appl. Phys. Vol. 38, April 1999, pp. 2306-9					
	15	Suzuki et al. "Effect of Post-oxidation-annealing in Hydrogen on SiO ₂ /4H-SiC Interface," Materials Science Forum, Vols. 338-342 (2000) 1073-6.					
	16	Leonhard et al. "Long term stability of gate-oxides on n- and p-type silicon carbide studied by charge injection techniques," Materials Science Engineering, Vol. 46, No. 1-3, April 1997, pp. 263-6.					
	17	Fukuda et al. "Improvement of SiO ₂ /4H-SiC Interface by Using High Temperature Hydrogen Annealing at 1000° C," Extended Abstracts of the International Conference on Solid State Devices and Materials. Japan Society of Applied Physics, Tokyo, Japan, Sept. 1998.					
<i>JKTH</i>	18	Chang et al. "Observation of a Non-stoichiometric Layer at the Silicon Dioxide--Silicon Carbide Interface: Effect of Oxidation Temperature and Post-Oxidation Processing Conditions." Mat. Res. Soc. Symp. Proc.					